

Test Report

日期(Date): 05-May-2021 號碼(No.): EKR21401999 頁數(Page): 1 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

高雄市楠梓加工出口區內環北路107號 (NO.26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN, R.O.C.)

以下測試樣品係由申請廠商所提供及確認 (The following sample(s) was/were submitted and identified by/on behalf of the applicant as):

送樣廠商(Sample Submitted By)

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

樣品名稱(Sample Name)

12" 晶圓(WAFER)

樣品型號(Style/Item No.)

電鍍銅(PLATING COPPER)

______ 收件日(Sample Receiving Date)

26-Apr-2021

測試期間(Testing Period)

26-Apr-2021 to 04-May-2021

測試需求(Test Requested)

- (1)依據客戶指定,參考RoHS 2011/65/EU Annex II及其修訂指令(EU) 2015/863測 試鎘、鉛、汞、六價鉻、多溴聯苯、多溴聯苯醚, DBP, BBP, DEHP, DIBP。 (As specified by client, with reference to RoHS 2011/65/EU Annex II and amending Directive (EU) 2015/863 to determine Cadmium, Lead, Mercury, Cr(VI), PBBs, PBDEs, DBP, BBP, DEHP, DIBP contents in the submitted
- (2) 其他測試項目請見下一頁。 (Please refer to next pages for the other item(s).) 請參閱下一頁 (Please refer to following pages.)

測試結果(Test Results)

論(Conclusion)

根據客戶所提供的樣品,其編、鉛、汞、六價鉻、多溴聯苯、多溴聯苯醚, DBP, BBP, DEHP, DIBP的測試結果符合RoHS 2011/65/EU Annex II暨其修訂指令(EU) 2015/863之限值要求。 (Based on the performed tests on submitted

sample(s), the test results of Cadmium, Lead, Mercury, Cr(VI), PBBs, PBDEs, DBP, BBP, DEHP, DIBP comply with the limits as set by RoHS Directive (EU)

2015/863 amending Annex II to Directive 2011/65/EU.)

Ray Chang, Ph.D./ Department Manager Signed for and on behalf SĞS TAIWAN LTD. 化學實驗室-高雄/Chemical Laboratory-Kaohsiung



PIN CODE: A036AB38



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號碼(No.): EKR21401999 日期(Date): 05-May-2021

頁數(Page): 2 of 17

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測試部位敘述 (Test Part Description)

No.1 : 銀色/銅色 12" 晶圓(WAFER) (SILVER/COPPER COLORED 12" 晶圓(WAFER))

測試結果 (Test Results)

測試項目 (Test Items)	測試方法 (Method)	單位 (Unit)	MDL	結果 (Result)	限值 (Limit)
				No.1	
鎘 (Cd) (Cadmium (Cd)) (CAS No.: 7440-43-9)	參考IEC 62321-5: 2013 · 以感應耦合電漿 發射光譜儀分析。(With reference to IEC 62321-5: 2013, analysis was performed by ICP-OES.)	mg/kg	2	n.d.	100
鉛 (Pb) (Lead (Pb)) (CAS No.: 7439-92-1)	參考IEC 62321-5: 2013 · 以感應耦合電漿 發射光譜儀分析。(With reference to IEC 62321-5: 2013, analysis was performed by ICP-OES.)	mg/kg	2	n.d.	1000
汞 (Hg) (Mercury (Hg)) (CAS No.: 7439-97-6)	参考IEC 62321-4: 2013+ AMD1: 2017·以 感應耦合電漿發射光譜儀分析。(With reference to IEC 62321-4: 2013+ AMD1: 2017, analysis was performed by ICP-OES.)	mg/kg	2	n.d.	1000
六價鉻 (Hexavalent Chromium) Cr(VI) (CAS No.: 18540-29-9)	參考IEC 62321-7-2: 2017·以紫外光-可見 光分光光度計分析。(With reference to IEC 62321-7-2: 2017, analysis was performed by UV-VIS.)	mg/kg	8	n.d.	1000
一溴聯苯 (Monobromobiphenyl)		mg/kg	5	n.d.	-
二溴聯苯 (Dibromobiphenyl)		mg/kg	5	n.d.	-
三溴聯苯 (Tribromobiphenyl)		mg/kg	5	n.d.	-
四溴聯苯 (Tetrabromobipenyl)	 參考IEC 62321-6: 2015,以氣相層析儀/質	mg/kg	5	n.d.	-
五溴聯苯 (Pentabromobiphenyl)	· 普(BC 62321-6. 2013 · 以来相層和 (B) · 普(集分析。(With reference to IEC 62321-6: 2015, analysis was performed by GC/MS.)	mg/kg	5	n.d.	-
六溴聯苯 (Hexabromobiphenyl)		mg/kg	5	n.d.	-
七溴聯苯 (Heptabromobiphenyl)		mg/kg	5	n.d.	-
八溴聯苯 (Octabromobiphenyl)		mg/kg	5	n.d.	-
九溴聯苯 (Nonabromobiphenyl)		mg/kg	5	n.d.	-
十溴聯苯 (Decabromobiphenyl)		mg/kg	5	n.d.	-
多溴聯苯總和 (Sum of PBBs)		mg/kg	-	n.d.	1000



Test Report

號碼(No.): EKR21401999 日期(Date): 05-May-2021

頁數(Page): 3 of 17

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(Method) (Unit) (Result) (Limit) No.1	測試項目	測試方法	單位	MDL	結果	限值
演勝苯醚 (Monobromodiphenyl ether)	(Test Items)	(Method)	(Unit)		(Result)	(Limit)
三溴聯苯醚 (Dibromodiphenyl ether) 日次					No.1	
三溴聯苯醚 (Tribromodiphenyl ether) 四溴聯苯醚 (Tetrabromodiphenyl ether) 多者IEC 62321-6: 2015・以氣相層析儀/質	· · · · · · · · · · · · · · · · · · ·		mg/kg	5	n.d.	-
四溴聯苯離 (Tetrabromodiphenyl ether)	二溴聯苯醚 (Dibromodiphenyl ether)		mg/kg	5	n.d.	-
大浪聯苯離 (Pentabromodiphenyl ether)	三溴聯苯醚 (Tribromodiphenyl ether)		mg/kg	5	n.d.	-
通貨勝本醚 (Pentabromodiphenyl ether)	•		mg/kg	5	n.d.	-
大漢聯本縣 (Hexatormodiphenyl ether) 日本		•	mg/kg	5	n.d.	-
C/MS. GC/MS. GC/		-	mg/kg		n.d.	-
大泉聯苯離 (Octabromodiphenyl ether) 大泉聯苯離 (Nonabromodiphenyl ether) 大泉聯苯離 (Decabromodiphenyl ether) 大泉聯苯離 (Decabromodiphenyl ether) 大泉聯苯離總和 (Sum of PBDEs) 大家 (Sb) (Antimony (Sb)) (CAS No.: 7440 多考US EPA 3052: 1996 · 以感應耦合電漿			mg/kg	5	n.d.	-
+ 決勝苯醚 (Decabromodiphenyl ether) 多溴聯苯醚總和 (Sum of PBDEs) 夢(Sb) (Antimony (Sb)) (CAS No.: 7440-36-0) 毅 (Sb) (Antimony (Sb)) (CAS No.: 7440-36-0) 毅 (Be) (Beryllium (Be)) (CAS No.: 7440-41-7) 多氨氯聯苯 (PCBs) (Polychlorinated by ICP-OES.) 多氮氯素 (PCNs) (Polychlorinated naphthalene (PCNs)) 多氮氯三聯苯 (PCTs) (Polychlorinated terphenyls (PCTs)) 多氨氯三酚苯 (PCTs) (Polychlorinated 分析。(With reference to US EPA 3550C: 2007 · 以氣相層析儀/質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 多氨氯三酚苯 (PCTs) (Polychlorinated 表示OC: 2007 · 以氣相層析儀/質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 多氨氯三酚苯 (PCTs) (Polychlorinated 表示OC: 2007 · 以氣相層析儀/質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 多氮三酚苯 (PCTs) (Polychlorinated 发表US EPA 3550C: 2007 · 以氣相層析儀/質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 多規述 (PCTs) (Polychlorinated 发表US EPA 3550C: 2007 · 以氣相層析儀/質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 知識就可能 (PCTs) (Polychlorinated 发表US EPA 3550C: 2007 · 以氣相層析儀/質 mg/kg 50 n.d 数別表 (PCTs) (Polychlorinated 数别表 (PCTs) (POlychlorinated 和表表		GC/1V13.)	mg/kg		n.d.	-
多漢聯苯醚總和 (Sum of PBDEs)	九溴聯苯醚 (Nonabromodiphenyl ether)		mg/kg	5	n.d.	-
### (Sb) (Antimony (Sb)) (CAS No.: 7440-36-0)			mg/kg	5	n.d.	-
36-0) 發射光譜儀分析。(With reference to US 飯 (Be) (Beryllium (Be)) (CAS No.: 7440-41-7)	多溴聯苯醚總和 (Sum of PBDEs)		mg/kg	ı	n.d.	1000
銀 (Be) (Beryllium (Be)) (CAS No.: 7440-41-7)	銻 (Sb) (Antimony (Sb)) (CAS No.: 7440-	參考US EPA 3052: 1996,以感應耦合電漿	mg/kg	2	n.d.	-
タ気職業 (PCBs) (Polychlorinated biphenyls (PCBs)) 多氯奈 (PCNs) (Polychlorinated biphenyls (PCBs)) 多氯奈 (PCNs) (Polychlorinated aphthalene (PCNs)) 多氯三聯苯 (PCTs) (Polychlorinated terphenyls (PCTs)) 参考US EPA 3550C: 2007・以氣相層析儀/質 mg/kg 5 n.d 質譜儀分析・(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 参考US EPA 3550C: 2007・以氣相層析儀/質 mg/kg 5 n.d 質譜儀分析・(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 参考US EPA 3550C: 2007・以氣相層析儀/質 mg/kg 0.5 n.d 要考US EPA 3550C: 2007・以氣相層析儀/質 mg/kg 50 n.d 基礎氯化石蠟(C10-C13) (SCCP) (Short 参考ISO 18219: 2015・以氣相層析儀/質 mg/kg 50 n.d	36-0)	發射光譜儀分析。(With reference to US				
多氯聯苯 (PCBs) (Polychlorinated biphenyls (PCBs)) 多氮奈 (PCNs) (Polychlorinated naphthalene (PCNs)) 多氮三聯苯 (PCTs) (Polychlorinated ferphenyls (PCTs)) 多氮三唑 (PCTs) (Polychlorinated ferphenyls (PCTs)) 多考US EPA 3550C: 2007 · 以氣相層析儀/ 所謂/ 以為相層析儀/ 所謂/ 以為相層析儀/ 所謂/ 以為相層析儀/ 所謂/ 以為表表表表表表表表表表表表表表表表表表表表表表表表表表表表表表表表表表表表	鈹 (Be) (Beryllium (Be)) (CAS No.: 7440-	EPA 3052: 1996, analysis was performed	mg/kg	2	n.d.	-
biphenyls (PCBs)) 質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 多氯奈 (PCNs) (Polychlorinated naphthalene (PCNs))	41-7)	by ICP-OES.)				
biphenyls (PCBs)) 質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 多氯奈 (PCNs) (Polychlorinated naphthalene (PCNs))	多氯聯苯 (PCBs) (Polychlorinated	參考US EPA 3550C: 2007,以氣相層析儀/	mg/kg	0.5	n.d.	-
3550C: 2007, analysis was performed by GC/MS.) 多氯奈 (PCNs) (Polychlorinated naphthalene (PCNs)) 多氯三聯苯 (PCTs) (Polychlorinated ferphenyls (PCTs)) 多第三聯苯 (PCTs) (Polychlorinated ferphenyls (PCTs)) 多第三聯苯 (PCTs) (Polychlorinated ferphenyls (PCTs)) 多考达 EPA 3550C: 2007 · 以氣相層析儀/質 mg/kg 0.5 n.d 多考US EPA 3550C: 2007 · 以氣相層析儀/質 mg/kg 0.5 n.d 多考证 是PA 3550C: 2007, analysis was performed by GC/MS.)		質譜儀分析。(With reference to US EPA	J. J			
多氯奈 (PCNs) (Polychlorinated naphthalene (PCNs)) 参考US EPA 3550C: 2007,以氣相層析儀/質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 参考US EPA 3550C: 2007,analysis was performed by GC/MS.) 参考US EPA 3550C: 2007,以氣相層析儀/質響/解析。(With reference to US EPA 3550C: 2007,analysis was performed by GC/MS.) 短鏈氯化石蠟(C10-C13) (SCCP) (Short 参考ISO 18219: 2015,以氣相層析儀/質 mg/kg 50 n.d		3550C: 2007, analysis was performed by				
maphthalene (PCNs)) 質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 多氯三聯苯 (PCTs) (Polychlorinated terphenyls (PCTs))		GC/MS.)				
maphthalene (PCNs)) 質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 多氯三聯苯 (PCTs) (Polychlorinated terphenyls (PCTs))	多氯奈 (PCNs) (Polychlorinated	參考US EPA 3550C: 2007,以氣相層析儀/	mg/kg	5	n.d.	-
Salight (PCTs) (Polychlorinated terphenyls (PCTs))	1 ' ' '	質譜儀分析。(With reference to US EPA	J. J			
多氯三聯苯 (PCTs) (Polychlorinated terphenyls (PCTs)) 参考US EPA 3550C: 2007,以氣相層析儀/質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.) 短鏈氯化石蠟(C10-C13) (SCCP) (Short 参考ISO 18219: 2015,以氣相層析儀/質 mg/kg 50 n.d		3550C: 2007, analysis was performed by				
terphenyls (PCTs)) 質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.)		GC/MS.)				
terphenyls (PCTs)) 質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.)	多氯三聯苯 (PCTs) (Polychlorinated	參考US EPA 3550C: 2007 · 以氣相層析儀/	mg/kg	0.5	n.d.	-
短鏈氯化石蠟(C10-C13) (SCCP) (Short 參考ISO 18219: 2015 · 以氣相層析儀/質 mg/kg 50 n.d. -	terphenyls (PCTs))	質譜儀分析。(With reference to US EPA	3 3			
短鏈氯化石蠟(C10-C13) (SCCP) (Short 参考ISO 18219: 2015·以氣相層析儀/質 mg/kg 50 n.d		3550C: 2007, analysis was performed by				
, , , , , , , , , , , , , , , , , , , ,		GC/MS.)				
	短鏈氯化石蠟(C10-C13) (SCCP) (Short	參考ISO 18219: 2015,以氣相層析儀/質	mg/kg	50	n.d.	-
Chain Chlorinated Paraffins(C10-C13) 譜儀分析。(With reference to ISO 18219:	Chain Chlorinated Paraffins(C10-C13)	譜儀分析。(With reference to ISO 18219:				
(SCCP)) (CAS No.: 85535-84-8) 2015, analysis was performed by	(SCCP)) (CAS No.: 85535-84-8)	2015, analysis was performed by				
GC/MS.)		GC/MS.)				



Test Report

號碼(No.): EKR21401999 日期(Date): 05-May-2021

頁數(Page): 4 of 17

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測試項目 (Test Items)	測試方法 (Method)	單位 (Unit)	MDL	結果 (Result) No.1	限值 (Limit)
氟 (F) (Fluorine (F)) (CAS No.: 14762-94-8)		mg/kg	50	n.d.	-
氯 (Cl) (Chlorine (Cl)) (CAS No.: 22537- 15-1)	参考BS EN 14582: 2016 · 以離子層析儀分析。(With reference to BS EN 14582:	mg/kg	50	n.d.	-
溴 (Br) (Bromine (Br)) (CAS No.: 10097- 32-2)	2016, analysis was performed by IC.)	mg/kg	50	n.d.	-
碘 (I) (Iodine (I)) (CAS No.: 14362-44-8)		mg/kg	50	n.d.	_
三丁基錫 (TBT) (Tributyl tin (TBT))	參考ISO 17353: 2004 · 以氣相層析儀/火	mg/kg	0.03	n.d.	-
三苯基錫 (TPhT) (Triphenyl tin (TPhT))	焰光度偵測器分析。(With reference to	mg/kg	0.03	n.d.	-
二丁基錫 (DBT) (Dibutyl tin (DBT))	ISO 17353: 2004, analysis was performed by GC/FPD.)	mg/kg	0.03	n.d.	-
二辛基錫 (DOT) (Dioctyl tin (DOT))	, ,	mg/kg	0.03	n.d.	-
氧化雙三丁基錫 (TBTO) (Bis(tributyltin) oxide (TBTO)) (CAS No.: 56-35-9)	由三丁基錫測試結果計算得之。 (Calculated from the result of Tributyl Tin (TBT).)	mg/kg	0.03▲	n.d.	-
全氟辛烷磺酸(PFOS)及其鹽類 (Perfluorooctane sulfonate (PFOS) and it's salt) (CAS No.: 1763-23-1 and its salts)	參考CEN/TS 15968: 2010 · 以液相層析串 聯質譜儀分析。(With reference to CEN/TS 15968: 2010, analysis was performed by LC/MS/MS.)	mg/kg	0.01	n.d.	-
全氟辛酸 (PFOA)及其鹽類 (Perfluorooctanoic acid (PFOA) and it's salt) (CAS No.: 335-67-1 and its salts)	參考CEN/TS 15968: 2010 · 以液相層析串 聯質譜儀分析。(With reference to CEN/TS 15968: 2010, analysis was performed by LC/MS/MS.)	mg/kg	0.01	n.d.	-
六溴環十二烷及所有主要被辨別出的異構物(HBCDD) (α- HBCDD, β- HBCDD, γ- HBCDD) (Hexabromocyclododecane (HBCDD) and all major diastereoisomers identified (α- HBCDD, β- HBCDD, γ- HBCDD)) (CAS No.: 25637-99-4, 3194-55-6 (134237-51-7, 134237-50-6, 134237-52-8))	參考IEC 62321: 2008·以氣相層析儀/質譜儀分析。(With reference to IEC 62321: 2008, analysis was performed by GC/MS.)	mg/kg	5	n.d.	-



Test Report

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頁數(Page): 5 of 17

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測試項目 (Test Items)	測試方法 (Method)	單位 (Unit)	MDL	結果 (Result)	限值 (Limit)
(Test items)	(ivietriod)	(Unit)		No.1	(LIIIIII)
聚氯乙烯 (Polyvinyl chloride) (PVC)	參考ASTM E1252: 2013 · 以傅立葉轉換紅外線光譜儀及焰色法分析。(With reference to ASTM E1252: 2013, analysis was performed by FT-IR and Flame Test.)	**	ı	Negative	-
可塑劑 (Phthalates)					
鄰苯二甲酸丁苯甲酯 (BBP) (Butyl benzyl phthalate (BBP)) (CAS No.: 85-68-7)	參考IEC 62321-8: 2017 · 以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	1000
鄰苯二甲酸二丁酯 (DBP) (Dibutyl phthalate (DBP)) (CAS No.: 84-74-2)	參考IEC 62321-8: 2017 · 以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	1000
鄰苯二甲酸二(2-乙基己基)酯 (DEHP) (Di-(2-ethylhexyl) phthalate (DEHP)) (CAS No.: 117-81-7)	參考IEC 62321-8: 2017 · 以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	1000
鄰苯二甲酸二異丁酯 (DIBP) (Diisobutyl phthalate (DIBP)) (CAS No.: 84-69-5)	參考IEC 62321-8: 2017 · 以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	1000
鄰苯二甲酸二異癸酯 (DIDP) (Diisodecyl phthalate (DIDP)) (CAS No.: 26761-40- 0, 68515-49-1)	參考IEC 62321-8: 2017 · 以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	-
鄰苯二甲酸二異壬酯 (DINP) (Diisononyl phthalate (DINP)) (CAS No.: 28553-12-0, 68515-48-0)	參考IEC 62321-8: 2017 · 以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	-
鄰苯二甲酸二正辛酯 (DNOP) (Di-n-octyl phthalate (DNOP)) (CAS No.: 117-84-0)	參考IEC 62321-8: 2017·以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	-



Test Report

號碼(No.): EKR21401999 日期(Date): 05-May-2021

頁數(Page): 6 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

高雄市楠梓加工出口區內環北路107號 (NO.26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN, R.O.C.)

備註(Note):

- 1. mg/kg = ppm; 0.1wt% = 1000ppm
- 2. MDL = Method Detection Limit (方法偵測極限值)
- 3. n.d. = Not Detected (未檢出); 小於MDL / Less than MDL
- 4. "-" = Not Regulated (無規格值)
- 5. **= Qualitative analysis (No Unit) 定性分析(無單位)
- 6. Negative = Undetectable 陰性(未偵測到); Positive = Detectable 陽性(已偵測到)
- 7. 全氟辛烷磺酸及其鹽類包含 (PFOS and its salts including):

CAS No.: 29081-56-9, 2795-39-3, 29457-72-5, 70225-14-8, 56773-42-3, 251099-16-8, 307-35-7.

- 8. 全氟辛酸及其鹽類包含 (PFOA and its salts including):
 - CAS No.: 3825-26-1, 335-95-5, 2395-00-8, 335-93-3, 335-66-0.
- 9. ▲: MDL是針對元素/測試化合物之評估。(The MDL was evaluated for element / tested substance.) 換算公式 (Conversion Formula): AX = A × F

AX	Α	F
氧化雙三丁基錫 (Bis(tributyltin)oxide) (TBTO)	三丁基錫 (Tributyl Tin) (TBT)	1.024

參數換算表 (Parameter Conversion Table):

https://eecloud.sgs.com/Region_TW/DocDownload.aspx#otherDoc

10. 符合性結果之判定係以測試結果與限值做比較。(The statement of compliance conformity is based on comparison of testing results and limits.)



Test Report

號碼(No.): EKR21401999 日期(Date): 05-May-2021

頁數(Page): 7 of 17

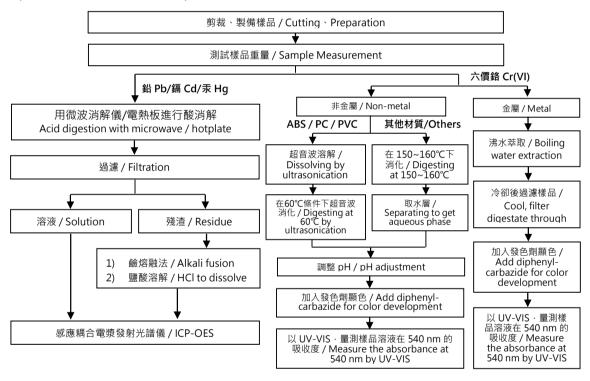
日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

高雄市楠梓加工出口區內環北路107號 (NO.26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN, R.O.C.)

重金屬流程圖 / Analytical flow chart of Heavy Metal

根據以下的流程圖之條件,樣品已完全溶解。(六價鉻測試方法除外)

These samples were dissolved totally by pre-conditioning method according to below flow chart. (Cr^{6+} test method excluded)





Test Report

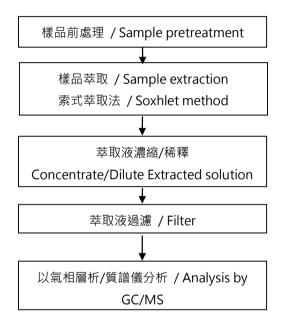
號碼(No.): EKR21401999 日期(Date): 05-May-2021

頁數(Page): 8 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

高雄市楠梓加工出口區內環北路107號 (NO.26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN, R.O.C.)

多溴聯苯/多溴聯苯醚 分析流程圖 / PBB/PBDE analytical FLOW CHART





Test Report

號碼(No.): EKR21401999 日期(Date): 05-May-2021

頁數(Page): 9 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

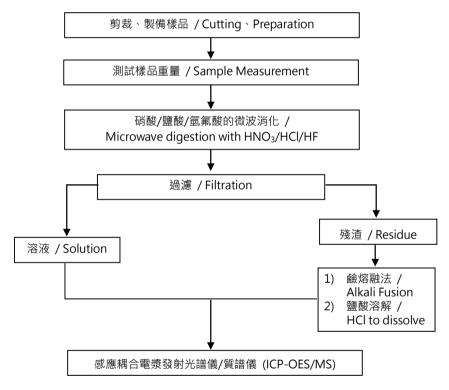
高雄市楠梓加工出口區內環北路107號 (NO.26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN, R.O.C.)

重金屬流程圖 / Analytical flow chart of Heavy Metal

根據以下的流程圖之條件,樣品已完全溶解。

These samples were dissolved totally by pre-conditioning method according to below flow chart.

【參考方法/Reference method: US EPA 3051、US EPA 3052】



* US EPA 3051 方法未添加氫氟酸 / US EPA 3051 method does not add HF.



Test Report

號碼(No.): EKR21401999 日期(Date): 05-May-2021

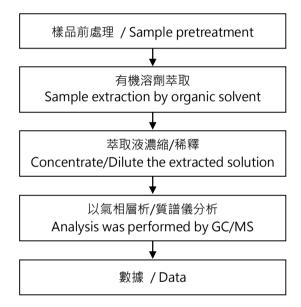
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分析流程圖 / Analytical flow chart

【適用於:多氯聯苯、多氯奈、多氯三聯苯、滅蟻靈、氯化石蠟、DBBT】

*Apply to: PCBs, PCNs, PCTs, Mirex, Chlorinated Paraffins, DBBT



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頁數(Page): 10 of 17



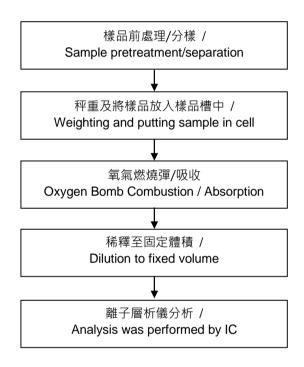
Test Report

號碼(No.): EKR21401999 日期(Date): 05-May-2021 頁數(Page): 11 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

高雄市楠梓加工出口區內環北路107號 (NO.26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN, R.O.C.)

鹵素分析流程圖 / Analytical flow chart of Halogen





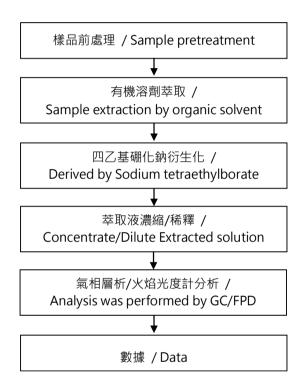
Test Report

號碼(No.): EKR21401999 日期(Date): 05-May-2021 頁數(Page): 12 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

高雄市楠梓加工出口區內環北路107號 (NO.26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN, R.O.C.)

有機錫分析流程圖 / Analytical flow chart - Organic-Tin





Test Report

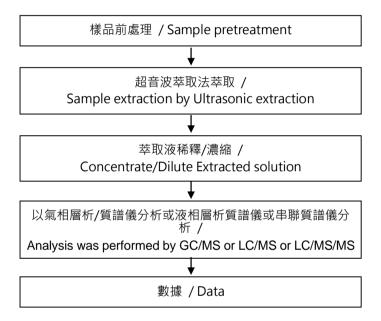
號碼(No.): EKR21401999 日期(Date): 05-May-2021

頁數(Page): 13 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

高雄市楠梓加工出口區內環北路107號 (NO.26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN, R.O.C.)

全氟化合物(包含全氟辛酸/全氟辛烷磺酸/其相關化合物等等)分析流程圖 / Analytical flow chart – PFAS (including PFOA/PFOS/its related compound, etc.)





Test Report

號碼(No.): EKR21401999 日期(Date): 05-May-2021

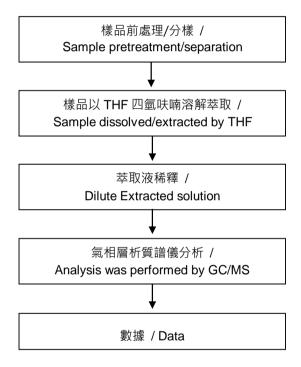
頁數(Page): 14 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

高雄市楠梓加工出口區內環北路107號 (NO.26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN, R.O.C.)

可塑劑分析流程圖 / Analytical flow chart of phthalate content

【測試方法/Test method: IEC 62321-8】





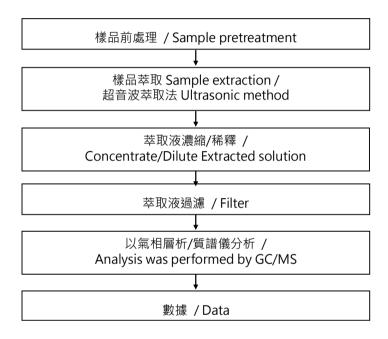
Test Report

號碼(No.): EKR21401999 日期(Date): 05-May-2021 頁數(Page): 15 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

高雄市楠梓加工出口區內環北路107號 (NO.26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN, R.O.C.)

六溴環十二烷分析流程圖 / Analytical flow chart - HBCDD





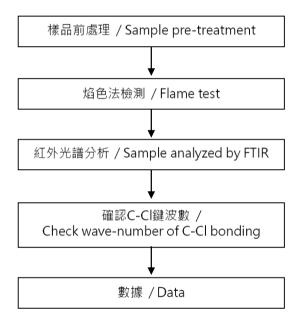
Test Report

號碼(No.): EKR21401999 日期(Date): 05-May-2021 頁數(Page): 16 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

高雄市楠梓加工出口區內環北路107號 (NO.26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN, R.O.C.)

聚氯乙烯物質判定分析流程圖 / Analysis flow chart - PVC





Test Report

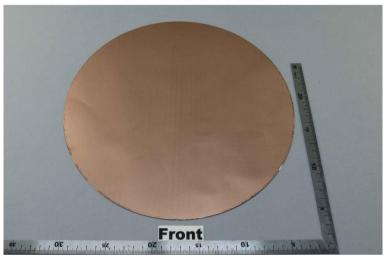
號碼(No.): EKR21401999 日期(Date): 05-May-2021 頁數(Page): 17 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.)

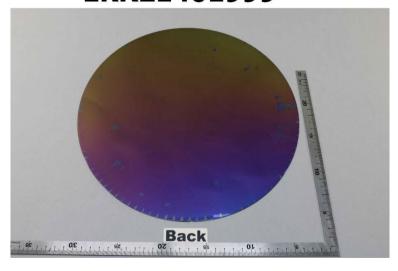
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* 照片中如有箭頭標示,則表示為實際檢測之樣品/部位. * (The tested sample / part is marked by an arrow if it's shown on the photo.)

EKR21401999



EKR21401999



** 報告結尾 (End of Report) **